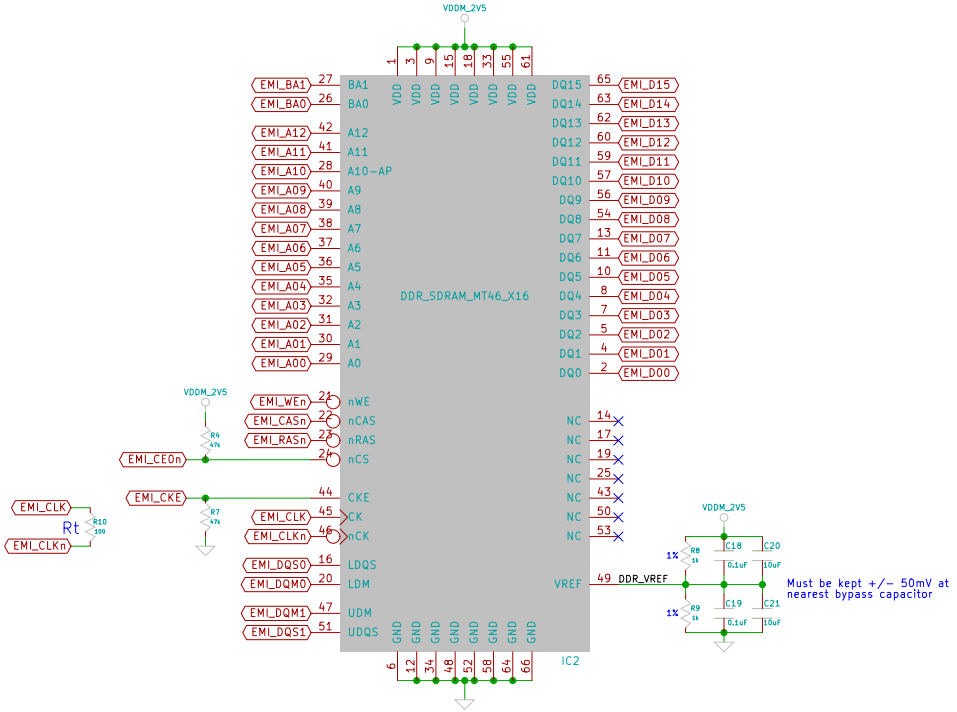
64Mbytes DDR SDRAM



Notes:
- All capacitors are X5R, 6.3V, 20%, ESR < 300mOhm or better unless otherwise noted
- All resistors are 5% unless otherwise noted
- Assuming 2-layer standard 1/16" FR4 (Dk=4.4, Df=0.02) and 7mil-7mil-15mil trace-space-drill design
- Per Micron TN-46-02, need about 7 0.1uF bypass caps but to fake TN-46-14 layout guidelines of GND planes use a lot more and consider external copper foil reference planes
- Cannot meet DDR routing guidelines (TN-46-14) on 2-layers so just keep all signals as short as possible to limit effects on Signal Integrity (SI) of incorrect inter/intra-pair spacing and characteristic trace impedance
- On 2-layer boards impedance of the lines is large so termination resistors should be used per TN-46-06.
- However, all the traces are < 0.8" long and therefore have an electrical length of <8deg at 200MHz. Also, most signals have only one via. Only UDQS (EMI_DQS1) has three vias. Since there is very little room anyway, do not use termination resistors.
- Only using one DDR device so should not require Rt and cannot fit it near i.MX233 IC anyway
- For additional design and layout notes see TN-46-11
- TN AppNotes are available at www.micron.com

DDR_VREF DDR_VREF

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